

Super-Junction Power Mosfet

1. Product Information

Features

- Surface-mounted package
- Super Junction technology
- Much lower FOM for fast switching efficiency

Applications

- Power supply
- Charger
- Solar/UPS-Micro inverter system

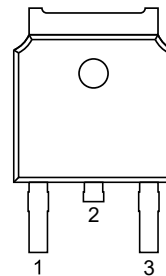
Quick reference

- $V_{DS} \geq 700\text{ V}$
- $I_D \leq 12\text{ A}$
- $R_{DS(ON)} \leq 360\text{ m}\Omega$ @ $V_{GS} = 10\text{ V}$ (Type 330 m Ω)

Pin Description

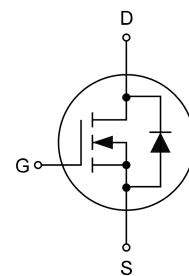
Pin	Description
1	Gate(G)
2	Drain(D)
3	Source(S)

Simplified Outline



Top View
TO-252-3L

Symbol



Package Marking and Ordering Information

Part number	Marking	Package	Packaging	Quantity	Reel size	Tape width
KJC70R360K	KJC70R360K	TO-252-3L	☒ Tape & Reel	2500 PCS	13"	16 mm
			☐ Tube	N/A	N/A	N/A

2. Absolute Maximum Ratings (T_C=25°C unless otherwise noted)

Symbol	Parameter	Values	Unit
V_{DS}	Drain-Source Voltage	700	V
V_{GS}	Gate-Source Voltage	±30	V
I_D	Continuous Drain Current (T _C =25°C)	12	A
	Continuous Drain Current (T _C =100°C)	7.6	A
I_{DM}	Pulsed Drain Current	36	A
E_{AS}	Single Pulsed Avalanche Energy (L=30 mH)	94	mJ
dv/dt	Peak Diode Recovery dv/dt	50	V/ns
I_S	Continuous diode forward current	12	A
P_D	Power Dissipation	130	W
T _J , T _{stg}	Operating Junction and Storage Temperature Range	-55 to 150	°C
$R_{\theta JA}$	Thermal Resistance, Junction-Ambient	95	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-Case	0.96	°C/W

3. Electrical Characteristics (T_J=25°C, unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Type	Max	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0 V, I _D =250 μA	700	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =700 V, V _{GS} =0 V	-	-	1	μA
		V _{DS} =700 V, T _C =150°C	-	10	-	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±30 V, V _{DS} =0 V	-	-	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250 μA	3.0	-	4.0	V
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =10 V, I _D =6 A	-	330	360	mΩ
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =100 V, V _{GS} =0 V, f=1 MHz	-	755	-	pF
C _{oss}	Output Capacitance		-	50	-	pF
C _{rss}	Reverse Transfer Capacitance		-	1.8	-	pF
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DS} =400 V, I _D =6 A, R _G =27 Ω, V _{GS} =10 V	-	22	-	ns
t _r	Turn-on Rise Time		-	25	-	ns
t _{d(off)}	Turn-off Delay Time		-	110	-	ns
t _f	Turn-off Fall Time		-	35	-	ns
R _g	Gate resistance	f=1 MHz	-	9.6	-	Ω
Q _g	Total Gate Charge	V _{DS} =520 V, I _D =6 A, V _{GS} =10 V	-	27	-	nC
Q _{gs}	Gate-Source Charge		-	4.5	-	nC
Q _{gd}	Gate-Drain Charge		-	13.5	-	nC
Source-Drain Diode Characteristics						
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} =0 V, I _F =6 A	-	0.85	1.1	V
Q _{rr}	Reverse Recovery Time	V _{DS} =100 V, I _F =6 A, di/dt=100 A/μs	-	2.1	-	μC
T _{rr}	Reverse Recovery Charge		-	221	-	ns

4. Electrical Characteristics

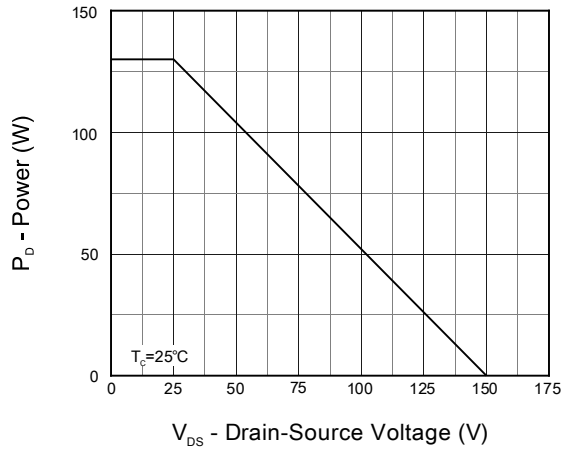


Fig 1. Output Characteristics

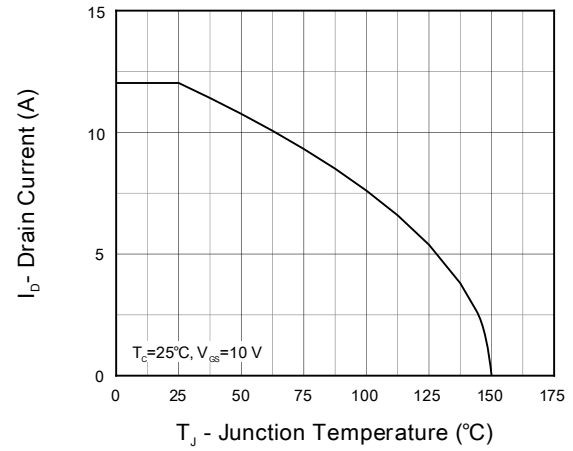


Fig 2. Current Capability

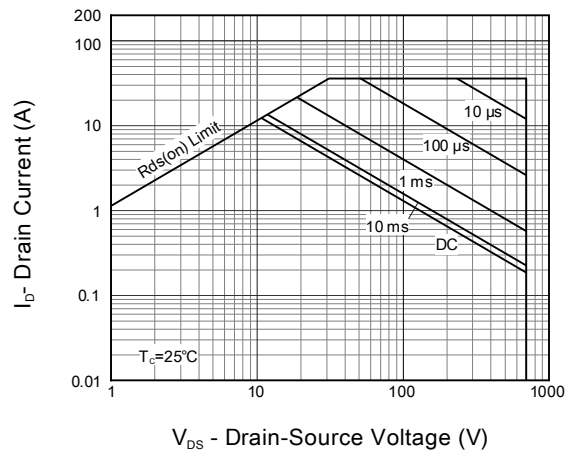


Fig 3. Safe Operation Area

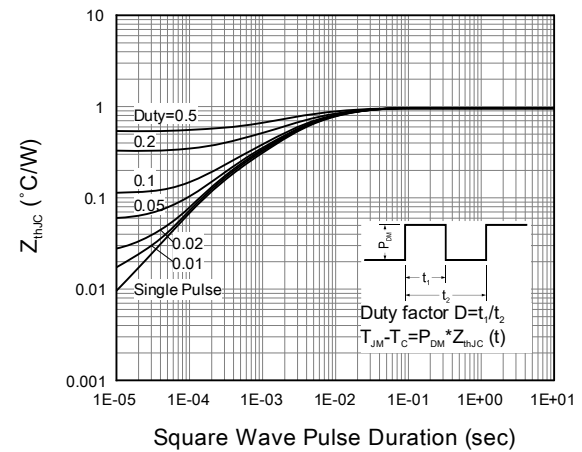


Fig 4. Transient Thermal Impedance

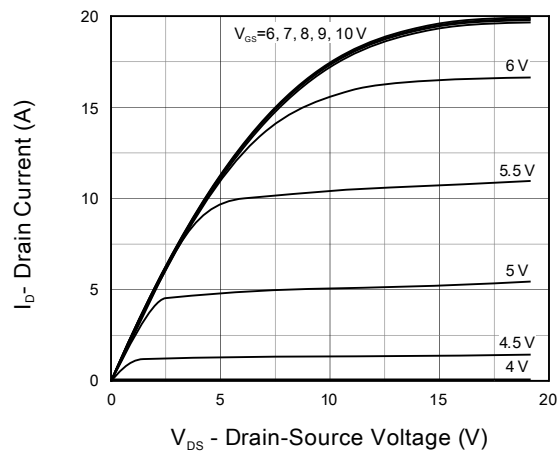


Fig 5. Output Characteristics
 $T_J = 25^\circ\text{C}$

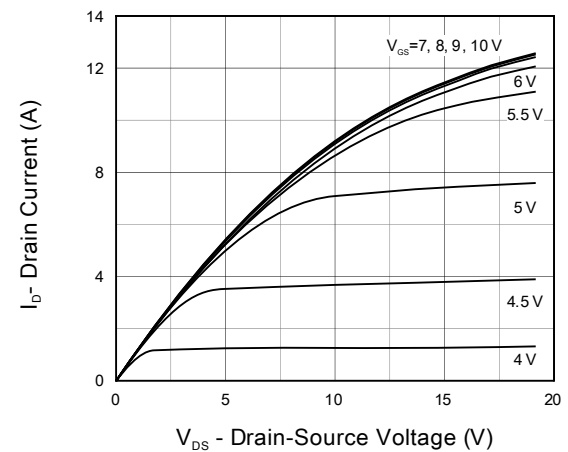
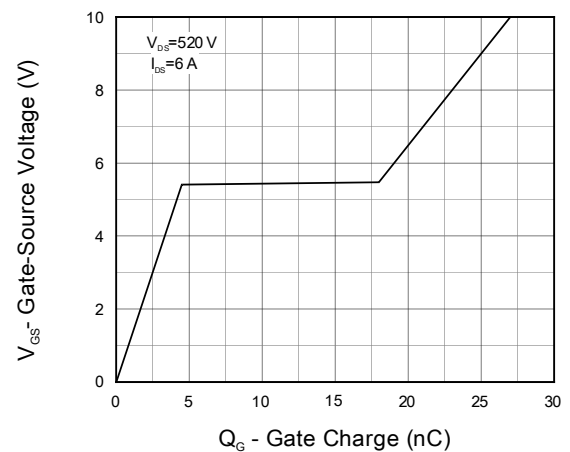
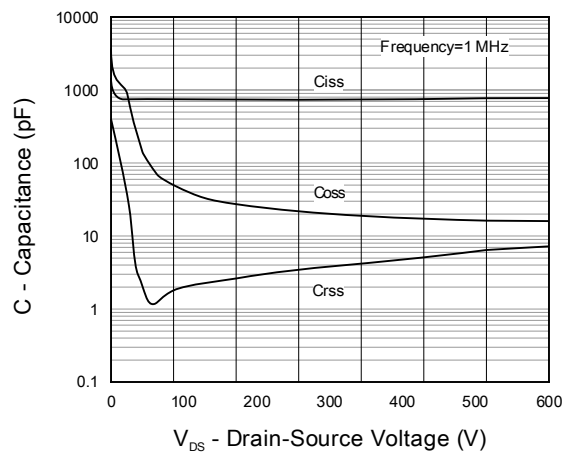
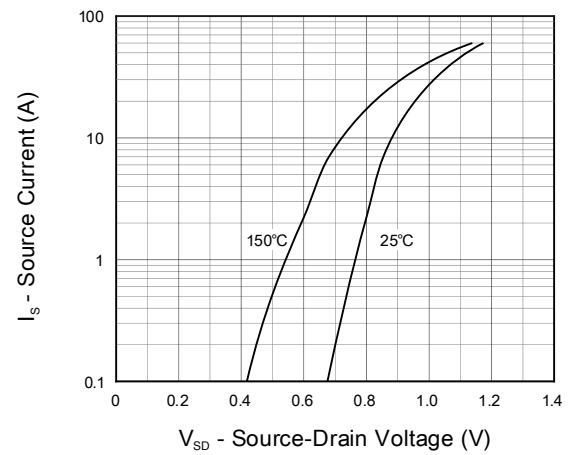
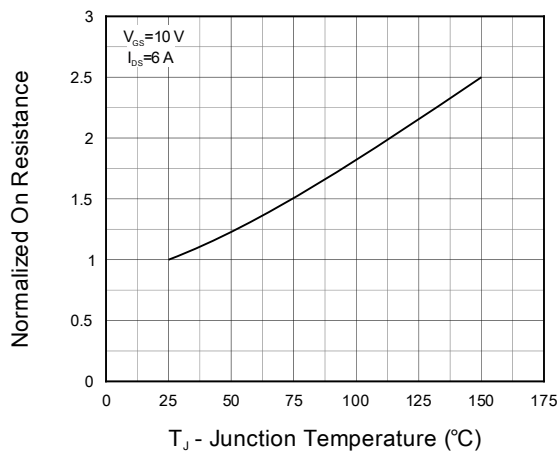
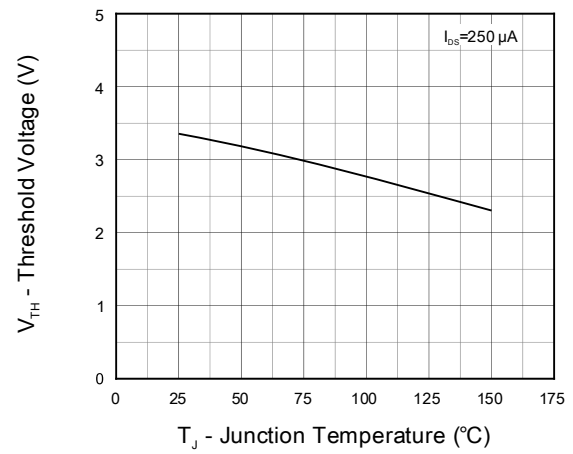
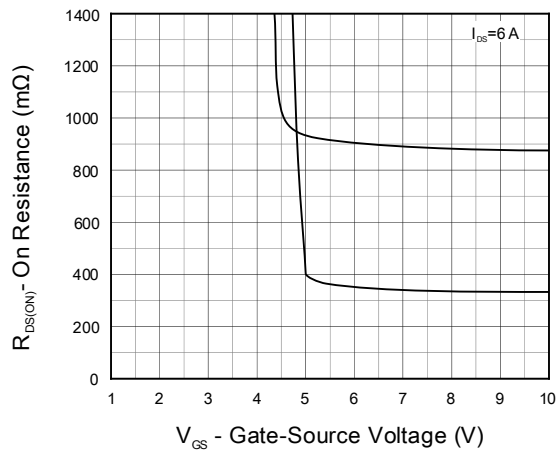


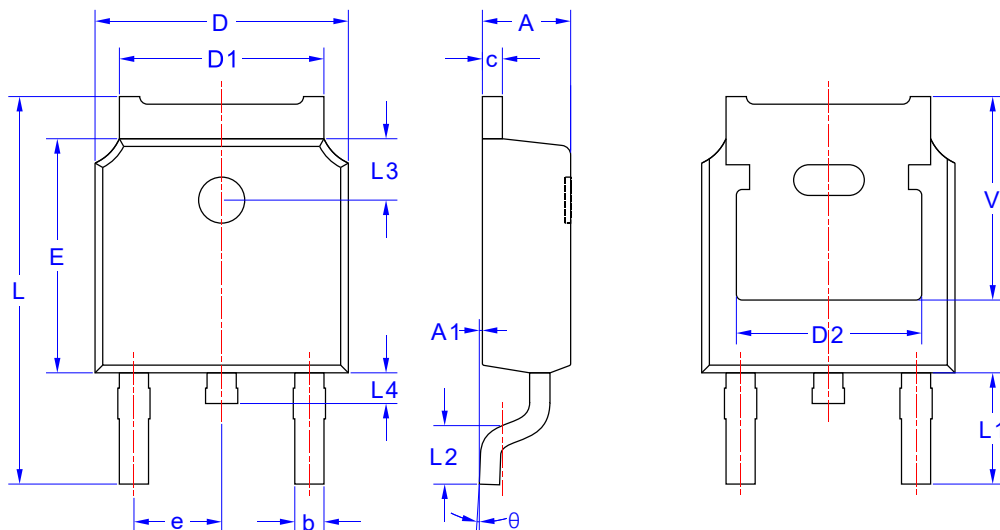
Fig 6. Output Characteristics
 $T_J = 150^\circ\text{C}$

5. Electrical Characteristics (cont.)



5. Package Mechanical Data

TO-252-3L Package



Symbol	Dimensions in Millimeters	
	MIN	MAX
A	2.200	2.400
A1	0	0.127
b	0.660	0.860
c	0.460	0.580
D	6.500	6.700
D1	5.100	5.460
D2	4.830 REF.	
E	6.000	6.200
e	2.186	2.386
L	9.800	10.400
L1	2.900 REF.	
L2	1.400	1.700
L3	1.800 REF.	
L4	0.600	1.000
θ	0°	8°
V	5.600 REF.	